CONTENTS

Preface
Conference committees and sponsors
Contents

Conference summary
KIMERLING, L.C., Defects in semiconductors – 1982 1

1. THEORY

TOYOZAWA, Y., Electron induced lattice relaxations and defect reactions, *(Invited paper)* 7
PANTELIDES, S.T., IVANOV, I., SCHEFFLER, M. and VIGNERON, J.P., Multivacancies, interstitials, and self-interstitial migration in silicon *(Invited paper)* 18
WATKINS, G.D., DELEO, G.G. and FOWLER, W.B., Theory defects in silicon: Recent calculations using finite molecular clusters *(Invited papers)* 28
SUMI, H., Carrier-density dependence of dynamic multiphonon nonradiative recombination through deep levels in semiconductors 39
MARKVART, T., Enhancement of defect reactions by tunnelling between defect potential curves 45
KUNC, K., Local force variations caused by isoelectric impurities: Method of determination from first principles 52
ZIGONE, M., VANDEVYVER, M. and TALWAR, D.N., Trend in the local-force variations due to substitutional transition-metal impurities in ZnS 58
LANNOO, M., A classification of the distortion symmetries near vacancies in zinc blende semiconductors 63
DAVIES, G., Distorted defects in silicon and diamond 66
JONES, R. and T. KING, Calculation of local density of states at defects in diamond and silicon 72
BARAFF, G.A., SCHLÜTER, M. and ALLAN, G., Calculation of Si and Al interstitials in silicon using the cluster-extended Green's function technique 76
KIRTON, M.J., JAROS, M. and BRAND, S., The electronic properties of dangling bonds in silicon 79
LANNOO, M. and BOURGOIN, J.C., A reexamination of the *g* tensor for defects with dangling bonds in silicon 85
FAZZIO, A., LEITE, J.R. and CALDAS, M.J., A molecular cluster study of complex defects in Si: the divacancy and the E center 90
MATHIOT, D. and PFISTER, J.C., On the diffusion of donors into silicon: high concentration and nonequilibrium defect effects 95
MAINWOOD, A. and STONEHAM, A.M., Interstitial muons and hydrogen in crystalline silicon 101
CALDAS, M.J., LEITE, J.R. and FAZZIO, A., Electronic structure of oxygen in silicon 106
PECHEUR, P. and TOUSSAINT, G., Tight binding study of transition ions in silicon and E.P.R. spectra 112
HEMSTREET, L.A., Electronic states of selected deep level defects in III–V semiconductors 116
VAN DER REST, J. and PECHEUR, P., Electronic density of states of ideal vacancies and anti-structure defects in GaAs 121
ANTONCIK, E. and GU, B.L., Internal electronic configuration of Sn donors and acceptors in $A^{III}B^{V}$ compounds 127
MORGAN, T.N., The electronic states of oxygen in gallium phosphide – An example of weak bonding 131

2. CRYSTAL GROWTH AND PROCESSING

ABE, T., HARADA, H. and CHIKAWA, J., Swirl defects in float-zoned silicon crystals *(Invited paper)* 139
CLAEYS, C., BENDER, H., DECLERCK, G., VAN LANDUYT, J., VAN OVERSTRAETEN, R. and AMELINCKX, S., Impact of high temperature processing on bulk defects in Czochralski silicon *(Invited paper)* 148
RICHTER, H., MAI, M., KIRSCHT, F.-G. and GAWORZEWSKI, P., Defect engineering as an important factor in developing VLSI substrates 162
RODOT, H., GUILLAUME, J.C., CHEVALLIER, J., BOULOU, M., KRIAPOV, V.T., KASHIMOV, F.R., MARKOVA, T.I. and ZOUBRIDSKI, I.A., Defects in gallium arsenide grown from solution under microgravity conditions 168

3. DIAMOND

MOSS, D.J., YOUNG, J.F., VAN DRIEL, H.M. and VERMEULEN, L.A., Time resolved donor–acceptor and acceptor–valence band recombination in semiconducting diamond 177
FLINT, I.T. and LOMER, J.N., The formation of the E.S.R. centres A-2 and A-3 in diamond electron irradiated below 30 K and an interpretation in terms of self di-interstitial complexes 183
GIPPIUS, A.A., VAVILOV, V.S., ZAITSEV, A.M. and ZHAKUPBEKOV, B.S., Defects production and interaction in ion-implanted diamond 187

4. SILICON

SAUER, R. and WEBER, J., Photoluminescence characterization of deep defects in silicon *(Invited paper)* 195
DE WAARD, H. and KEMERINK, G.J., Hyperfine interaction and channeling studies of impurities implanted in silicon *(Invited paper)* 210
NEWTON, J.L., CHATTERJEE, A.P., HARRIS, R.D. and WATKINS, G.D., Negative-U properties of the lattice vacancy in silicon 219
SPRENGER, M., MULLER, S.H. and AMMERLAAN, C.A.J., The negatively charged vacancy in silicon: Hyperfine interactions from ENDOR measurements 224
OEHRLEIN, G.S., LINDSTRÖM, J.L., KRAFCSIK, I., JAWOROWSKI, A.E. and CORBETT, J.W., A quantitative investigation of divacancy production enhancement by interstitial oxygen in electron-irradiated silicon 230
BAGRAEV, N.T., Electron localization on defects and optical nuclear polarization in disordered and semimagnetic semiconductors 236
KELLER, W., PENSL, G. and SCHULZ, M., Experimental study of the Poole–Frenkel effect on the Si:Tl acceptor 244
THONKE, K., WEBER, J., WAGNER, J. and SAUER, R., Origin of the 1.080 eV (I_2) photoluminescence line in irradiated silicon 252
O'DONNELL, K.P., LEE, K.M. and WATKINS, G.D., Origin of the 0.97 eV luminescence in irradiated silicon 258
NEWMAN, R.C., BINNS, M.J., BROWN, W.P., LIVINGSTON, F.M., MESSOLORAS, S., STEWART, R.J. and WILKES, J.G., Precipitation of oxygen in silicon: Kinetics, solubility, diffusivity and particle size 264
BENTON, J.L., KIMERLING, L.C. and STAVOLA, M., The oxygen related donor effect in silicon 271
FOY, C.P., Optical studies in vibronic bands in silicon 276
VLASENKO, L.S., Excited triplet states of defects and optical nuclear polarization in silicon 281
JAWOROWSKI, A.E., OEHRLEIN, G.S. and CORBETT, J.W., Electron irradiation effects in edge-defined film-fed growth ribbon silicon 287
CONZELMANN, H. and WEBER, J., Photoluminescence from chromium–boron pairs in silicon 291
KIMERLING, L.C. and BENTON, J.L., Electronically controlled reactions of interstitial iron in silicon 297
WÜNSTEL, K., FROEHNER, K.-H. and WAGNER, P., Iron-related defects in silicon 301
SCHIRMER, O.F., ESR of Fe–S pairs in silicon 306
BERGHOLZ, W., Pairing reactions of interstitial cobalt and shallow acceptors in silicon observed in Mössbauer spectroscopy 312
SCHEIBE, E. and SCHRÖTER, W., Investigations in cobalt doped silicon by DLTS and Mössbauer effect 318
KITAGAWA, H., HASHIMOTO, K. and YOSHIDA, M., Point defects in silicon studied by nickel diffusion 323
IWAMI, H., TROMP, R.M., VAN LOENEN, E.J. and SARIS, F.W., Enhancement of damage creation at metal–silicon interfaces during H^+ and He^+ irradiation 328
HENNING, J.C.M., The structure of the Pt center in silicon 332
STOLWIJK, N.A., SCHUSTER, B., HÖLZL, J., MEHRER, H. and FRANK, W., Diffusion and solubility of gold in silicon 335

5. GERMANIUM

FUKUOKA, N. and SAITO, H., The hole trapping defects in irradiated germanium as studied by DLTS 343
HALLER, E.E. and McMURRAY, R.E., Jr., Two novel acceptors in ultra-pure germanium: nature and interconversion 349
DÖRING, K.-P., HAAS, N., HALLER, E.E., HERLACH, D., JACOBS, W., KRAUTH, M., ORTH, H., ROSENKRANZ, J., SEEGER, A., VETTER, J., ARNOLD, K.-P., AURENZ, Th. and BOSSY, H., Muonium in ultra-pure germanium 354
KONOPLEVA, R.F., EVSEEV, V.A., BORISOV, B.A., NAZARKIN, I.V. and CHEKANOV, V.A., Using reactor-neutron compensated germanium crystals to simulate the properties of amorphous semiconductors 361

6. III-V COMPOUND

MARTIN, G.M. and MAKRAM-EBEID, S., Manifestations of deep level point defects in GaAs *(Invited paper)* 371
KOUIMTZI, S.D., Low temperature electron damage studies in n-type GaAs 384
PONS, D., Anisotropic defect introduction in n and p-GaAs by electron irradiation 388
STIEVENARD, D., BOURGOIN, J.C. and D. PONS, Defects introduced by high temperature electron irradiation in n-GaAs 394
WEBER, E.R. and SCHNEIDER, J., As_{Ga} antisite defects in GaAs 398
TAJIMA, M. and OKADA, Y., Characterization of deep levels in LEC GaAs crystals by the photoluminescence technique 404
PICOLI, G., DEVEAUD, B. and LAMBERT, B., Chromium in trigonal site in GaAs 409
POMRENKE, G.S., PARK, Y.S., HENGEHOLD, R.L. and MACLIN, M.T., Luminescence characteristics of the 1.4 eV silicon related complex in gallium arsenide 414
FRANK, W. and GÖSELE, U., A unifying interpretation of dark line defects in GaAs and bright dislocation halos in GaP 420
KILLORAN, N., CAVENETT, B.C., GODLEWSKI, M., KENNEDY, T.A. and WILSEY, N.D., Spin dependent formation and decay of the triplet antisite centre in GaP 425
MOONEY, P.M., KENNEDY, T.A. and SMALL, M.B., Correlated DLTS and EPR measurements of defects in As-grown and electron irradiated p-type GaP 431
FERENCZI, G., PAVELKA, T. and SOMOGYI, M., Identification of a deep electron trap in GaP:N 436
SHANABROOK, B.V., KLEIN, P.B. and BISHOP, S.G., Photoluminescence excitation spectroscopy of Fe-doped GaP 444
RAO, E.V.K., SIBILLE, A. and DUHAMEL, N., Investigation of process-induced defects in InP 449
BARRAU, J., DO XUAN THANH, BROUSSEAU, M., BRABANT, J.C. and VOILLOT, F., The zero-phonon luminescence from Cr^{2+} in InP 456
YUBA, Y., JUDAI, Y., GAMO, K. and NAMBA, S., OTCS study of defect state in Fe-doped semi-insulating InP induced by ion irradiation and thermal annealing 461
LAMBERT, B., DEVEAUD, B., TOUDIC, Y. and CLERJAUD, B., Electron paramagnetic resonance of InP:Co^{2+} 467
WEYER, G., PETERSEN, J.W. and DAMGAARD, S., The electronic configuration of amphoteric Sn dopants in III-V compound semiconductors 470
LOUALICHE, S., NOUAILHAT, A. and GUILLOT, G., Optical ionization cross sections of the traps created in 1 MeV electron irradiated n-type $Ga_{1-x}Al_xAs$ 474
WADA, T. and SAKURAI, K., 20 keV electron-beam annealing of defects in GaAsP during SEM measurement 479

7. II-VI COMPOUND

FITZPATRICK, B., NEUMARK, G., BHARGAVA, R. and VERMAAK, J., Structural defects and p-type conductivity in ZnSe *(Invited paper)* 487
WEST, C., ROBBINS, D., DEAN, P.J. and HAYES, W., The luminescence of copper in zinc oxide 492
CLERJAUD, B., GELINEAU, A., GENDRON, F., PORTE, C., BARANOWSKI, J.M. and LIRO, Z., Optical properties of $Ni^+(d^9)$ in ZnS 500
TAGUCHI, T., YOKOGAWA, T., FUJITA, S., SATOH, M. and INUISHI, Y., Defect creation and doping of p-type impurities in ZnS crystals 503
DEAN, P.J., PITT, A.D., WRIGHT, P.J., YOUNG, M.L. and COCKAYNE, B., The optoelectronic properties of donors in organo-metallic grown zinc selenide 508
SAMINADAYAR, K., COX, R.T., GALLAND, D. and LE SI DANG, EPR and ODMR investigations of defect centres in ZnTe:Cl 514
CHAMONAL, J.P., MOLVA, E., DUPUY, M., ACCOMO, R. and PAUTRAT, J.L., Spectral resolution in low temperature cathodoluminescence. Application to CdTe 519

8. LASER AND IONIZATION EFFECT

CULLIS, A.G., Defect structure transitions in silicon induced by Q-switched laser annealing *(Invited paper)* 527
MASHOVETS, T.V. and EMTSEV, V.V., Ionization mechanisms of defect production in semiconductors *(Invited paper)* 537
CHANTRE, A., KECHOUANE, M. and BOIS, D., Vacancy-diffusion model for quenched-in E-centers in CW laser annealed virgin silicon 547
SHENG, N.H. and MERZ, J.L., Fe-related defect centers in Si resulting from CW laser annealing 553
PEERCY, P.S., CALVIN, C.J., THOMPSON, M.O., MAYER, J.W. and HAMMOND, R.B., Measurements of the melt dynamics in laser annealed semiconductors 558
MURAKAMI, K., MASUDA, K., AOYAGI, Y. and NAMBA, S., Experimental tests for non-thermal effect for pulsed-laser annealing by time-resolved reflectivity and EPR measurements 564
SALATHÉ, K.P., GILGEN, H.H. and ZYSSET, B., Dynamical aspects of laser generating luminescence centers in (Al,Ga)As 570
VAN VECHTEN, J.A., Origin of CW laser generated high efficiency AlGaAs microstructures 575

9. DISLOCATION

ALEXANDER, H., KISIELOWSKI-KEMMERICH, C. and WEBER, E.R., Investigations of well defined dislocations in silicon *(Invited paper)* 583
KÜSTERS, K.H. and ALEXANDER, H., Photoplastic effect in silicon 594
OURMAZD, A., WILSHAW, P.R. and BOOKER, G.R., The electrical behaviour of individual dislocations, Shockley partials and stacking fault ribbons in silicon 600
OSHIMA, R., SADAMITSU, S. and FUJITA, F.E., High voltage electron microscope study of defects in silicon 606
VIEGERS, M.P.A., BULLE-LIEUWMA, C.W.T. and BARTELS, W.J., Overcompensation of misfit strain by dislocation networks in phosphorus implanted (001) silicon 612
HIRATA, M. and KIRITANI, M., Formation of vacancy and interstitial clustered defects in electron irradiated germanium 616
HIRATA, M. and KIRITANI, M., Thermal shrinkage of dislocation loops and the mechanism of self-diffusion in germanium 623
SNYMAN, H.C. and NEETHLING, J.H., Dislocation and void formation in proton-bombarded and annealed gallium arsenide 629
STEWART, C.P., BLUNT, R.T., BOOKER, G.R. and SANDERS, I.R., TEM damage studies and electrical profile measurements of Si^+ implanted GaAs 635
FNAIECH, M. and LOUCHET, F., Dislocation structures and in situ observations of dislocation motion in InSb 641
LU, G. and COCKAYNE, J.H., Dislocation structures and motion in II–VI semiconductors 646
HUTSON, A.R., Charge transport by dislocations in II–VI compounds 650

List of contributors 657
Analytic subject index 659